

Thin-Film PV Technologies

CIGS PV Technology

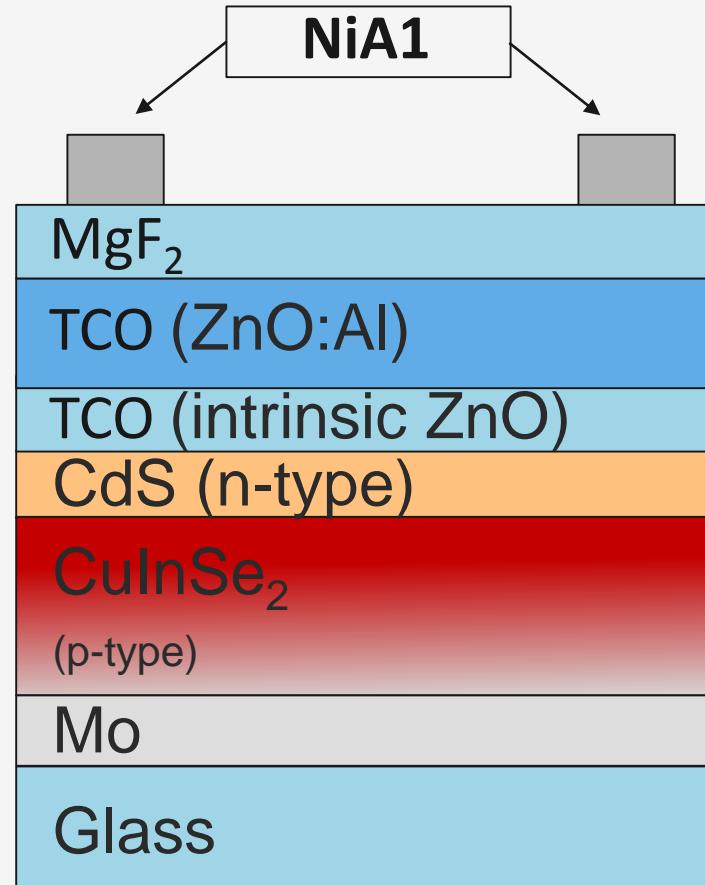
Week 5.3

Arno Smets



Challenge the future

CIGS



CIGS

IV-semiconductors:

III-V semiconductors:

II-VI semiconductors

The periodic table shows the following elements highlighted in yellow circles:

- Copper (Cu)
- Gallium (Ga)
- Indium (In)
- Sulfur (S)
- Selenium (Se)

The table also includes the following information:

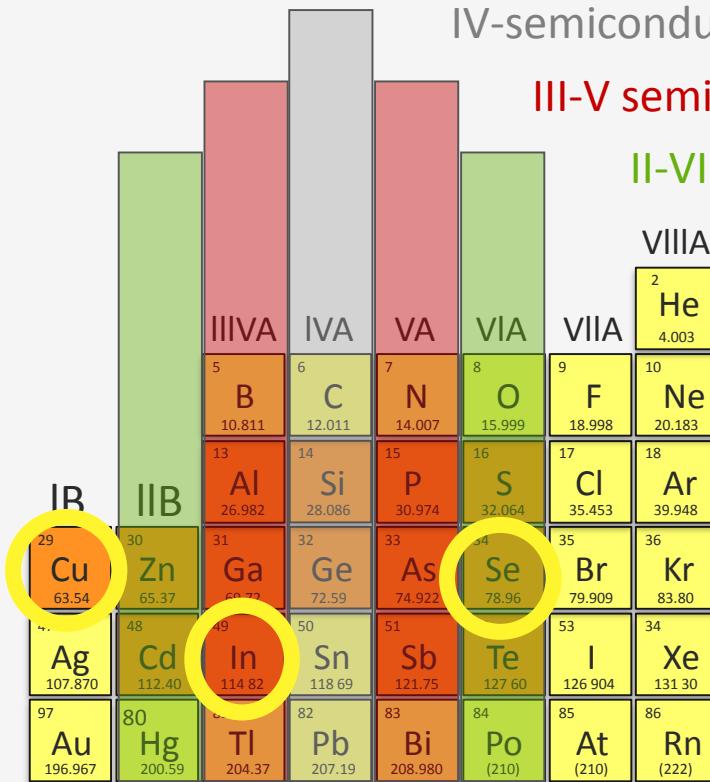
Group	Element	Atomic Number	Symbol	Atomic Mass
IB	Copper	29	Cu	63.54
IIB	Zinc	30	Zn	65.37
IIIA	Aluminum	13	Al	26.982
IVA	Silicon	14	Si	28.086
VA	Phosphorus	15	P	30.974
VIA	Arsenic	33	As	74.922
VIIA	Sulfur	16	S	32.064
VIIIA	Chlorine	17	Cl	35.453
	Bromine	35	Br	79.909
	Kr	36	Kr	83.80
	Xe	34	Xe	131.30
	Rn	86	Rn	(222)
	Gold	97	Au	196.967
	Hg	80	Hg	200.59
	Thallium	81	Tl	204.37
	Pb	82	Pb	207.19
	Bismuth	83	Bi	208.980
	Po	84	Po	(210)
	At	85	At	(210)
	Rn	86	Rn	(222)

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IV-semiconductors:

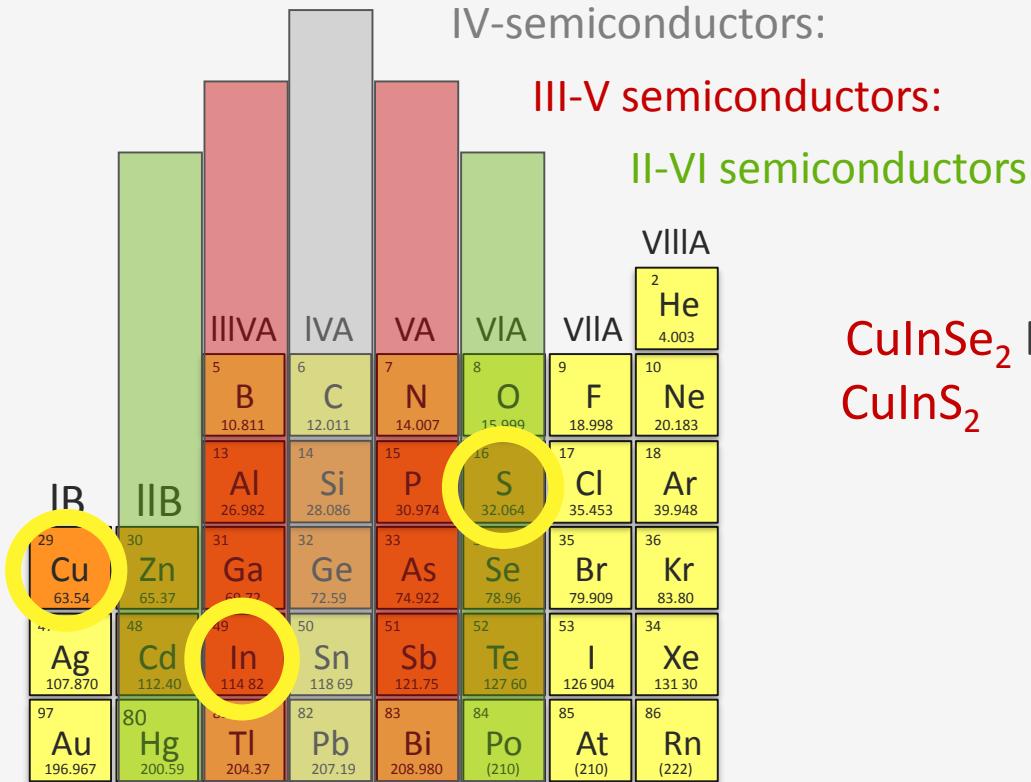
III-V semiconductors:

II-VI semiconductors



CuInSe₂ E_{gap} = 1.0 eV

CIGS



IV-semiconductors:

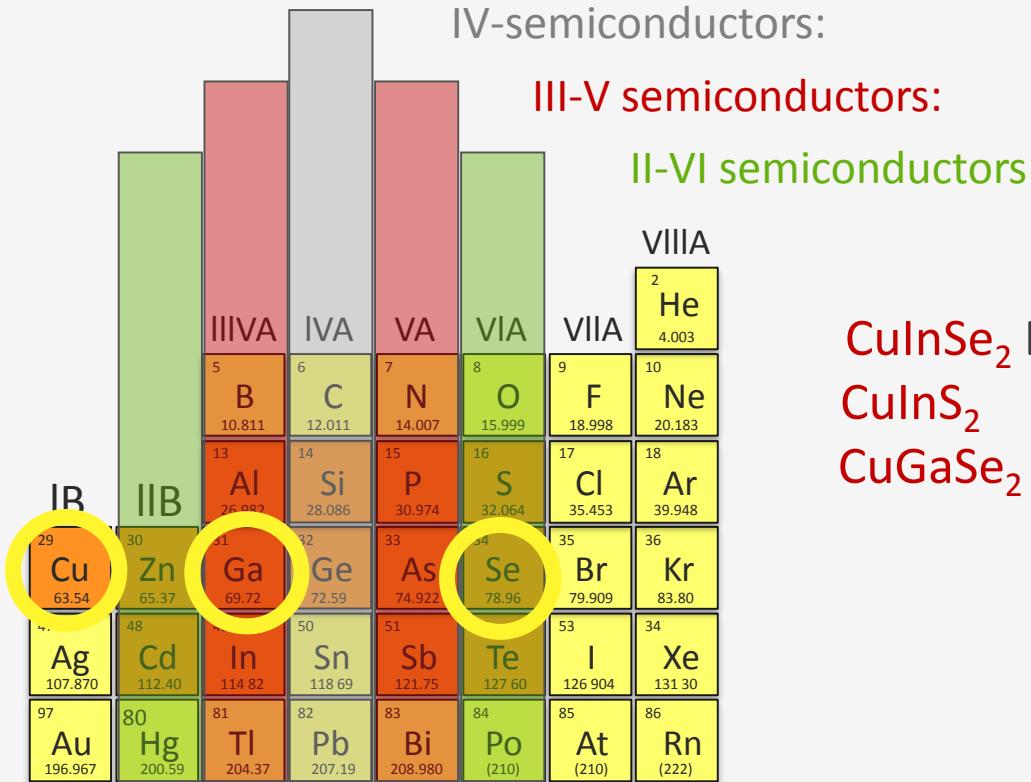
III-V semiconductors:

II-VI semiconductors

CuInSe_2 $E_{\text{gap}} = 1.0 \text{ eV}$

CuInS_2 $E_{\text{gap}} = 1.5 \text{ eV}$

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IV-semiconductors:

III-V semiconductors:

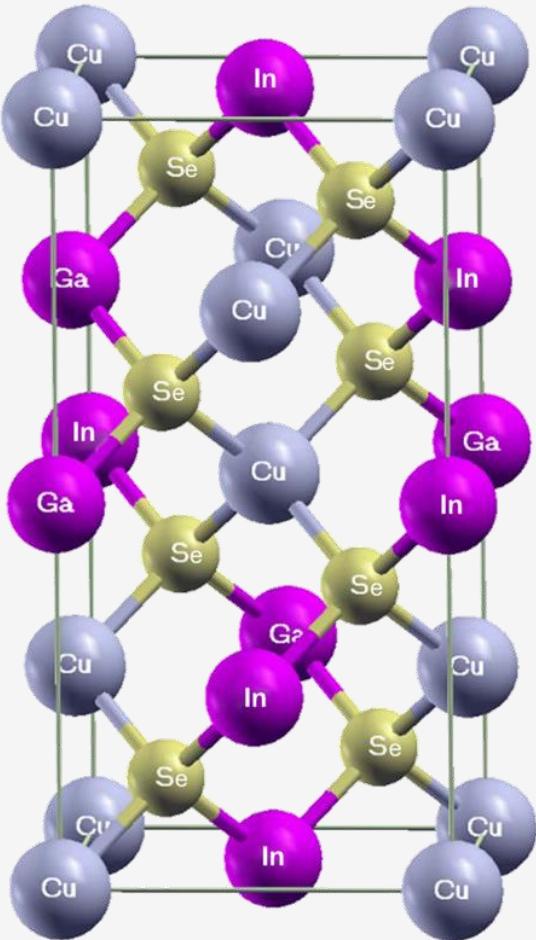
II-VI semiconductors

CuInSe_2 $E_{\text{gap}} = 1.0 \text{ eV}$

CuInS_2 $E_{\text{gap}} = 1.5 \text{ eV}$

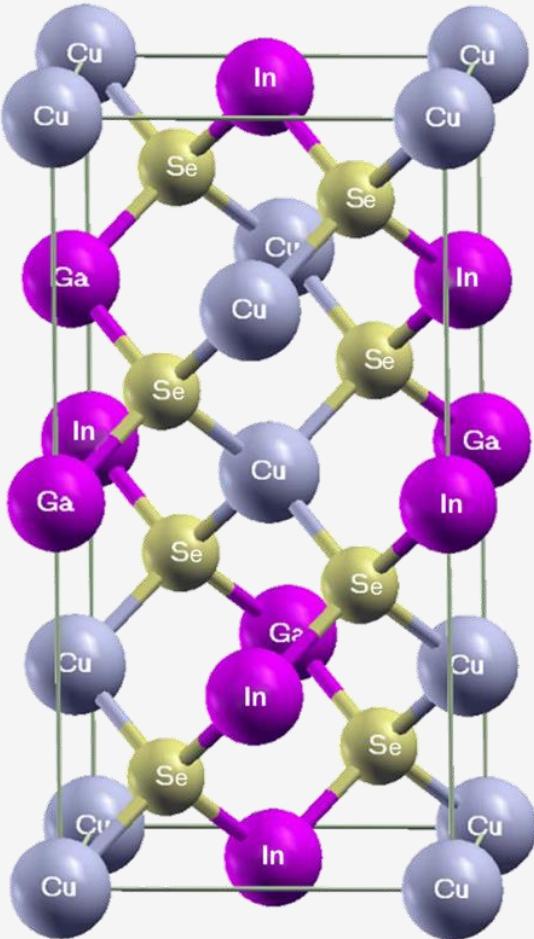
CuGaSe_2 $E_{\text{gap}} = 1.7 \text{ eV}$

CIGS



Chen and Gong, PRB **75**, 205209 (2007)

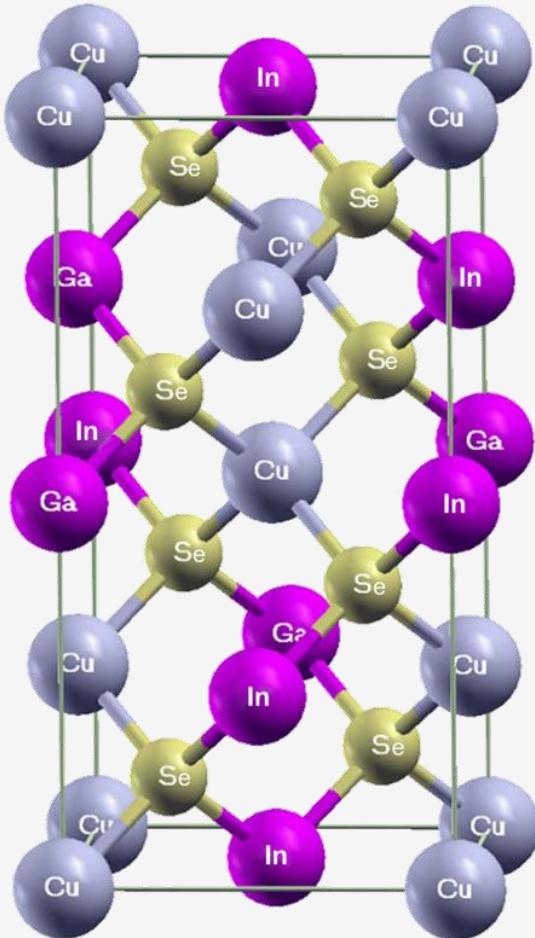
CIGS



CIS: CuInSe_2 $E_{\text{gap}} = 1.0 \text{ eV}$

Chen and Gong, PRB **75**, 205209 (2007)

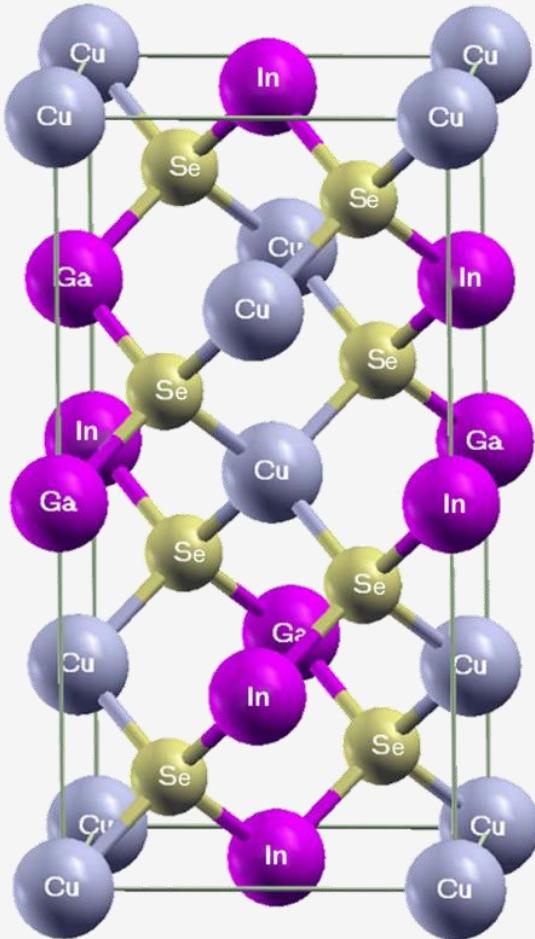
CIGS



CIS: CuInSe_2 $E_{\text{gap}} = 1.0 \text{ eV}$

$\text{CuIn}_x\text{Ga}_{1-x}\text{Se}_2$ $E_{\text{gap}} = 1.5 \text{ eV}$

CIGS

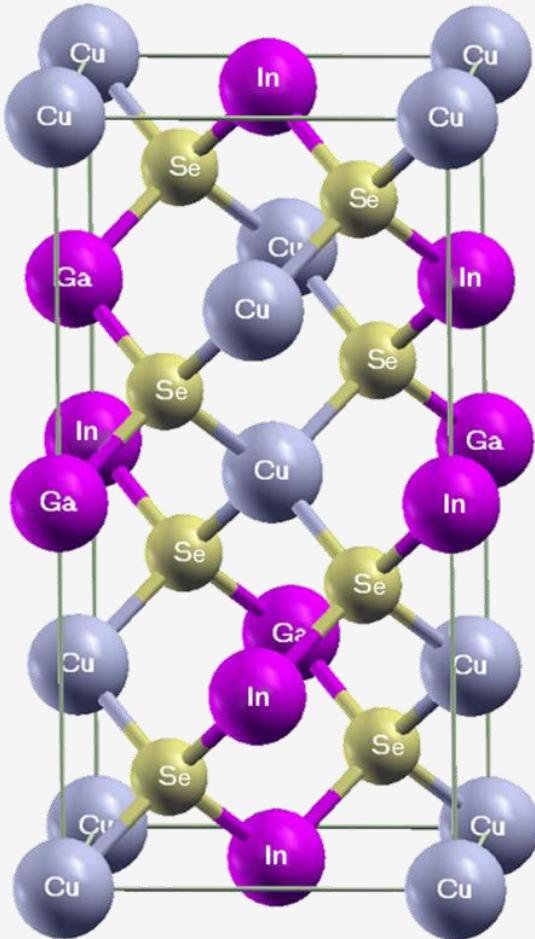


CIS: CuInSe_2 $E_{\text{gap}} = 1.0 \text{ eV}$

$\text{CuIn}_x\text{Ga}_{1-x}\text{Se}_2$ $E_{\text{gap}} = 1.5 \text{ eV}$

$x=0$ CuGaSe_2 $E_{\text{gap}} = 1.7 \text{ eV}$

CIGS



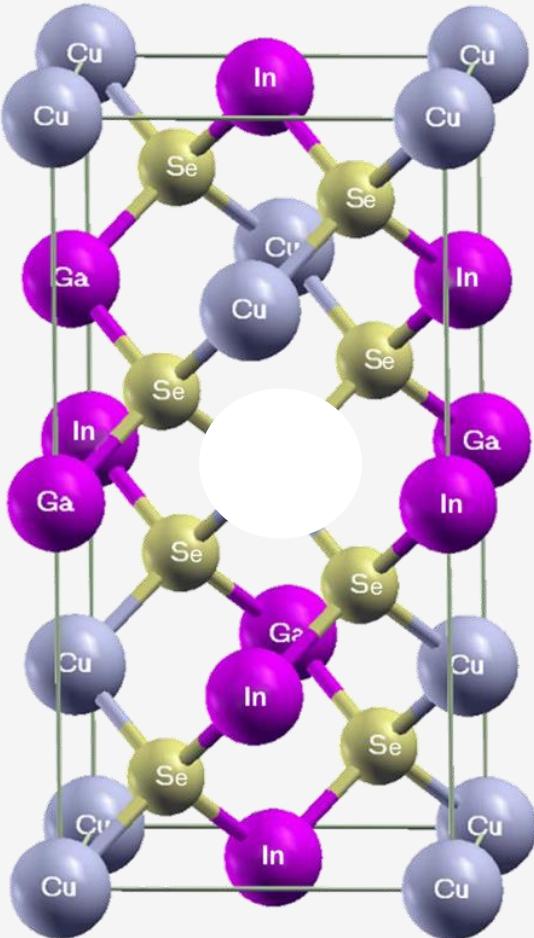
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$\text{CuIn}_x\text{Ga}_{1-x}\text{Se}_2$ $E_{\text{gap}} = 1.5 \text{ eV}$

$x=0$ CuGaSe_2 $E_{\text{gap}} = 1.7 \text{ eV}$

$x=1$ CuInSe_2 $E_{\text{gap}} = 1.0 \text{ eV}$

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P-type

Cu deficiencies

Chen and Gong, PRB **75**, 205209 (2007)

CIGS solar cell



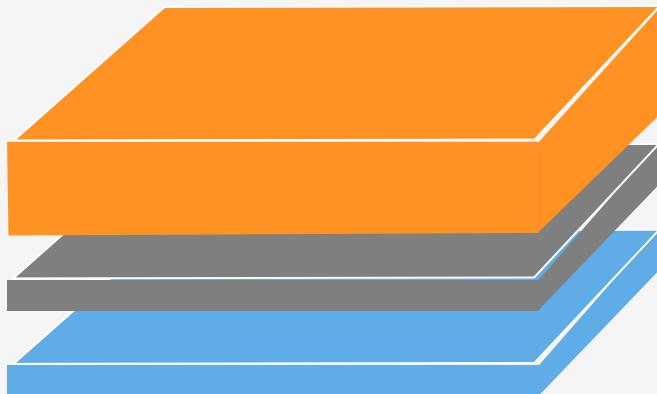
Glass

CIGS solar cell



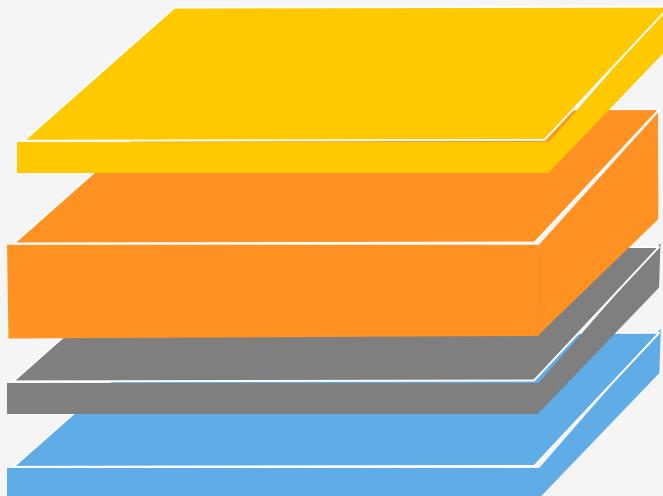
Mo
Glass

CIGS solar cell



P-type CIGS
Mo
Glass

CIGS solar cell



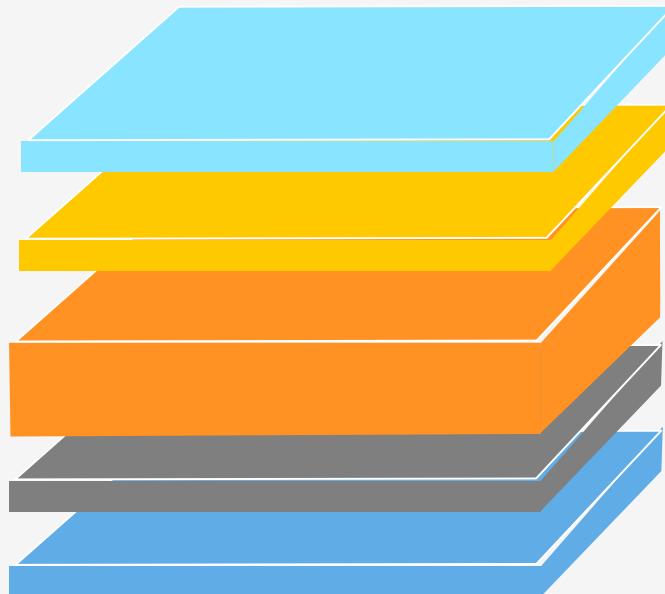
CdS Buffer

P-type CIGS

Mo

Glass

CIGS solar cell



i-ZnO

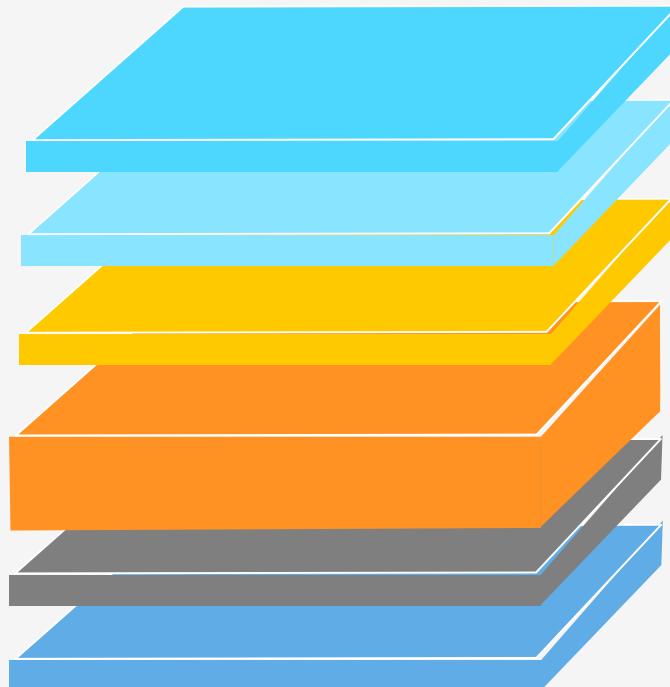
CdS Buffer

P-type CIGS

Mo

Glass

CIGS solar cell



Al-ZnO

i-ZnO

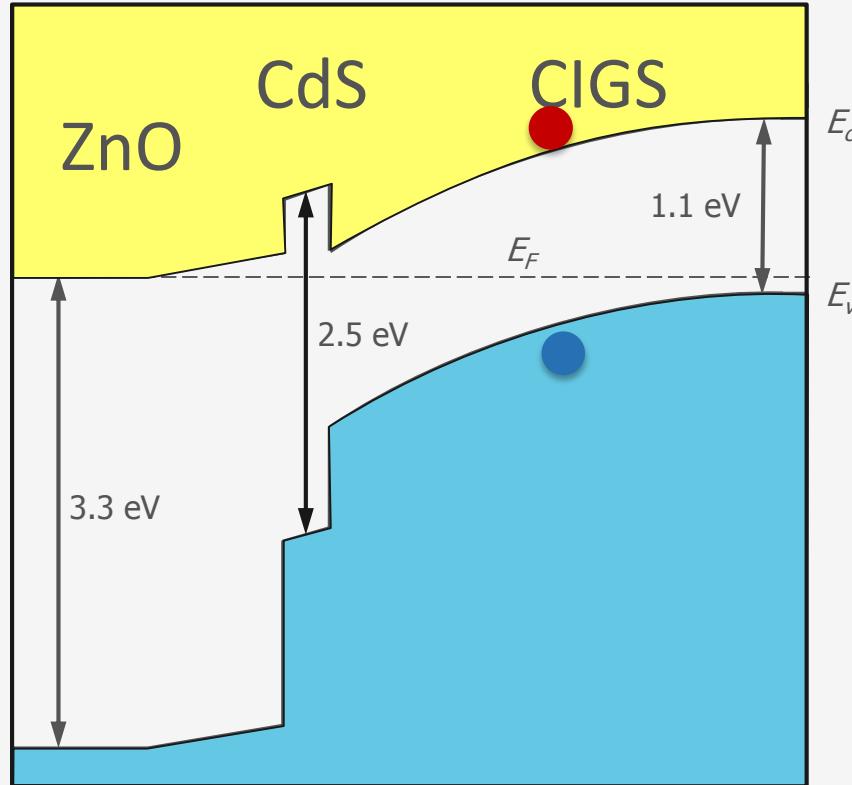
CdS Buffer

P-type CIGS

Mo

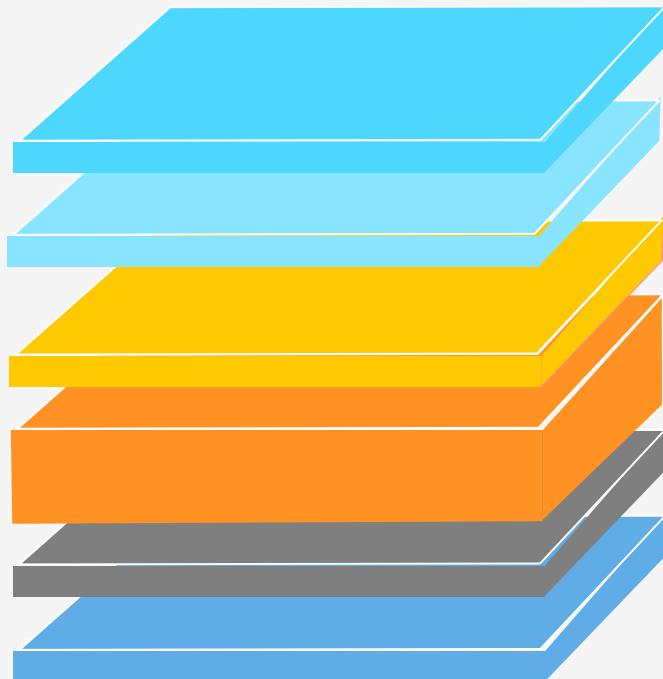
Glass

CI(G)S solar cell band diagram



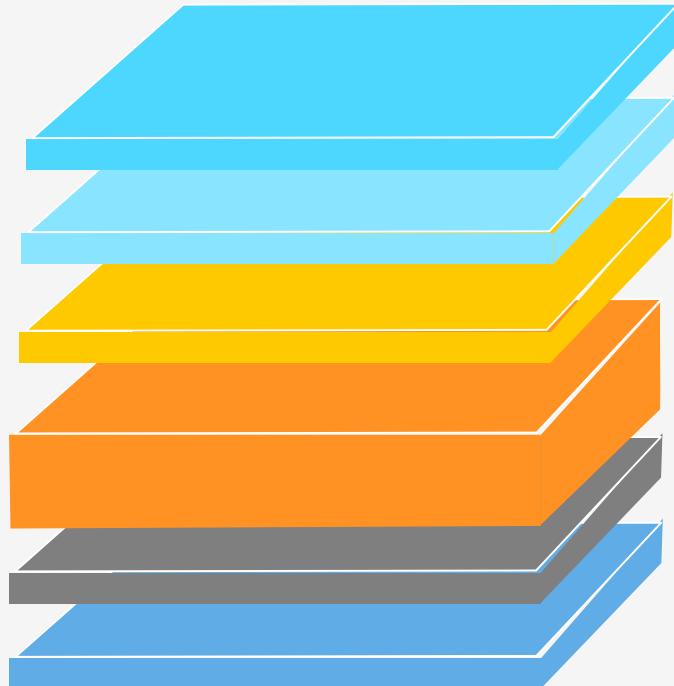
CIGS solar cell

n-type CIGS
 $\text{Cu}(\text{InGa})_3\text{Se}_5$



Al-ZnO
i-ZnO
CdS Buffer
P-type CIGS
Mo
Glass

Role Sodium in CIGS solar cells



Al-ZnO

i-ZnO

CdS Buffer

P-type CIGS

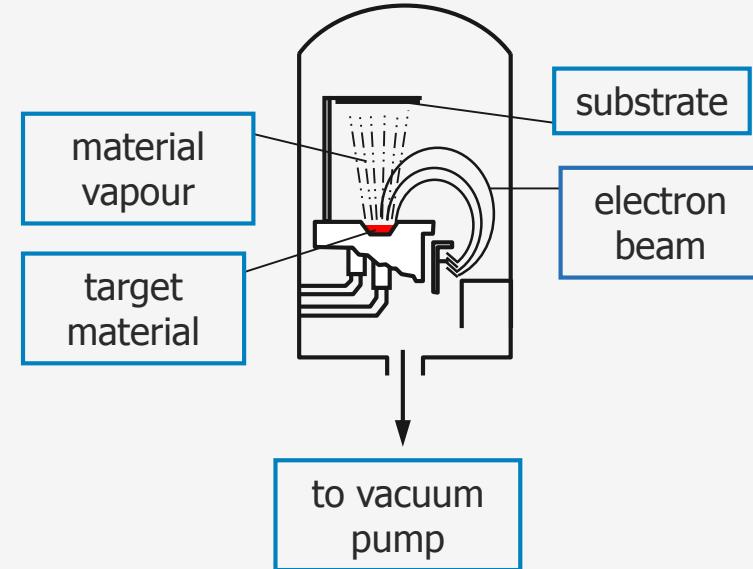
Mo

Glass

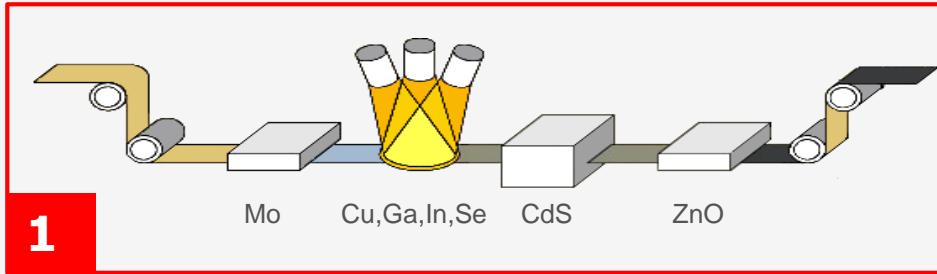
Sputtering deposition



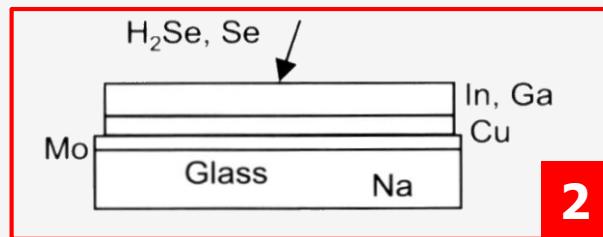
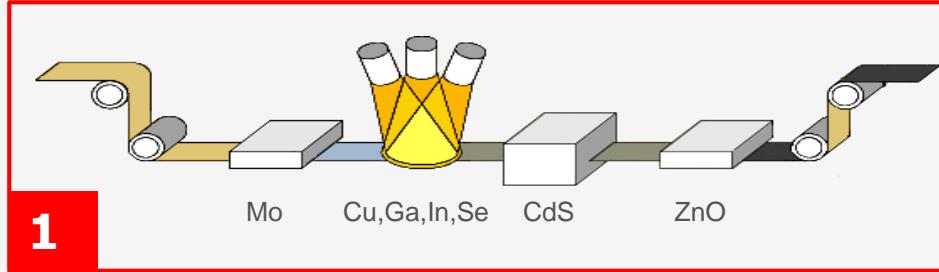
Co-evaporation



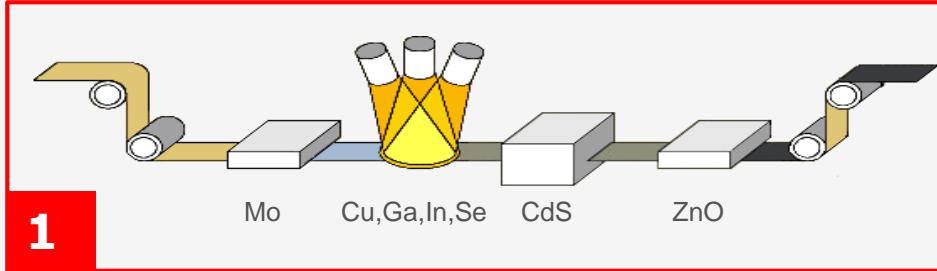
Processing CIGS solar cells



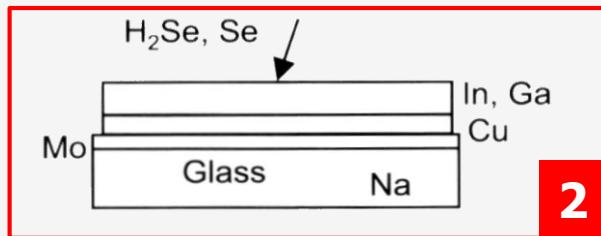
Processing CIGS solar cells



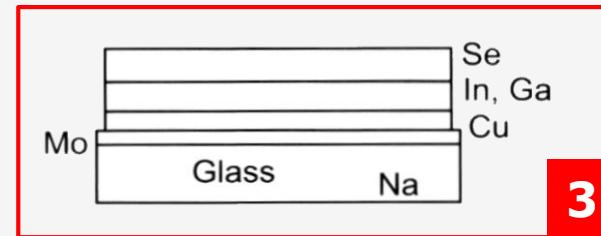
Processing CIGS solar cells



1

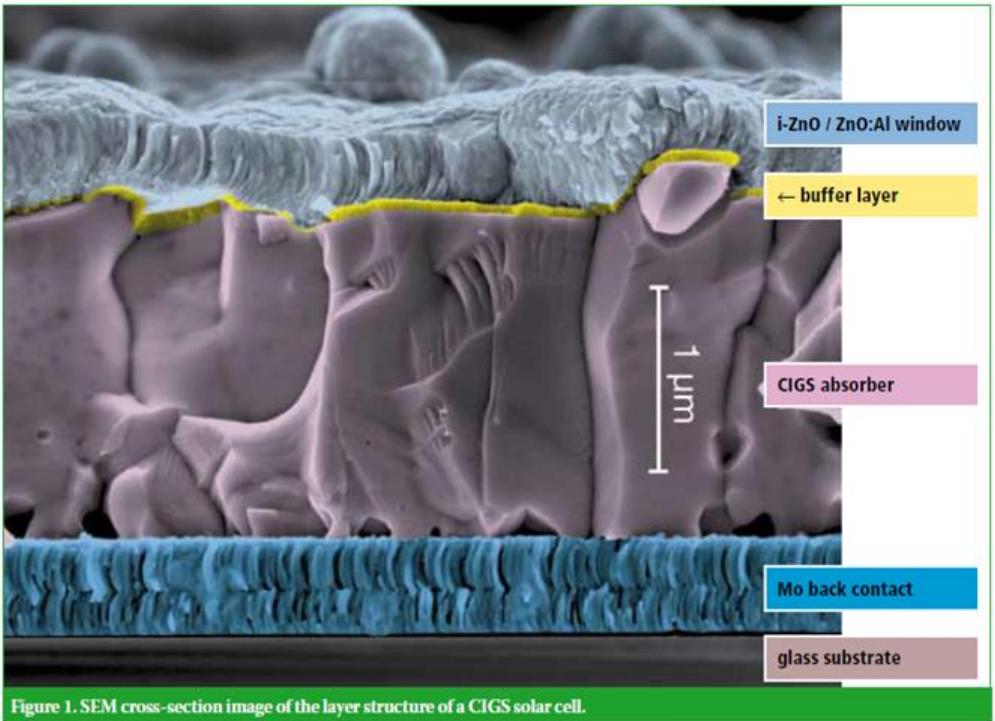


2



3

Labscale CIGS solar cells



Glass

NREL:

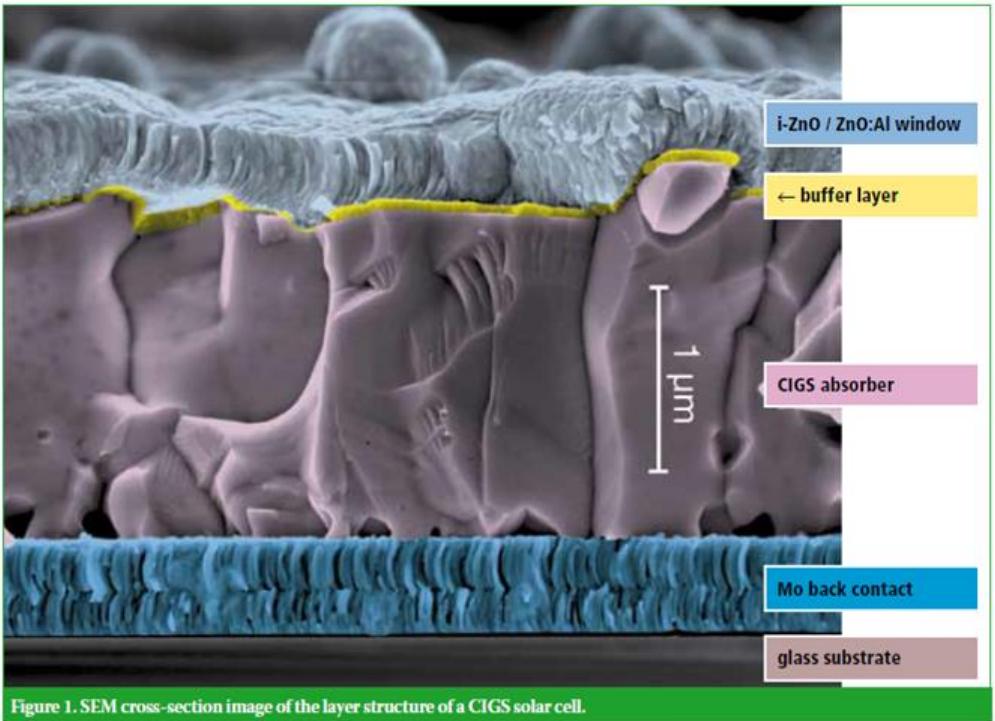
Eff = 19.9 %

Voc ~ 700 mV

J_{sc} ~ 35-36 mA cm⁻²

FF = 81 %

Labscale CIGS solar cells



Glass

NREL:

Eff = 19.9 %

Voc ~ 700 mV

J_{sc} ~ 35-36 mAcm⁻²

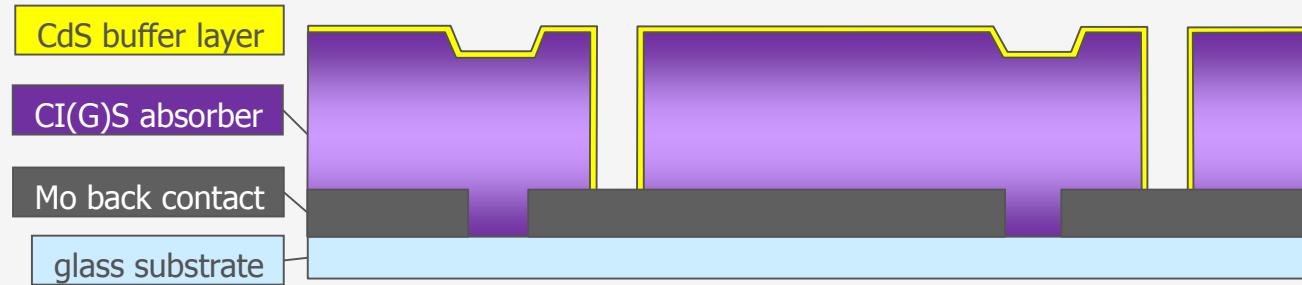
FF = 81 %

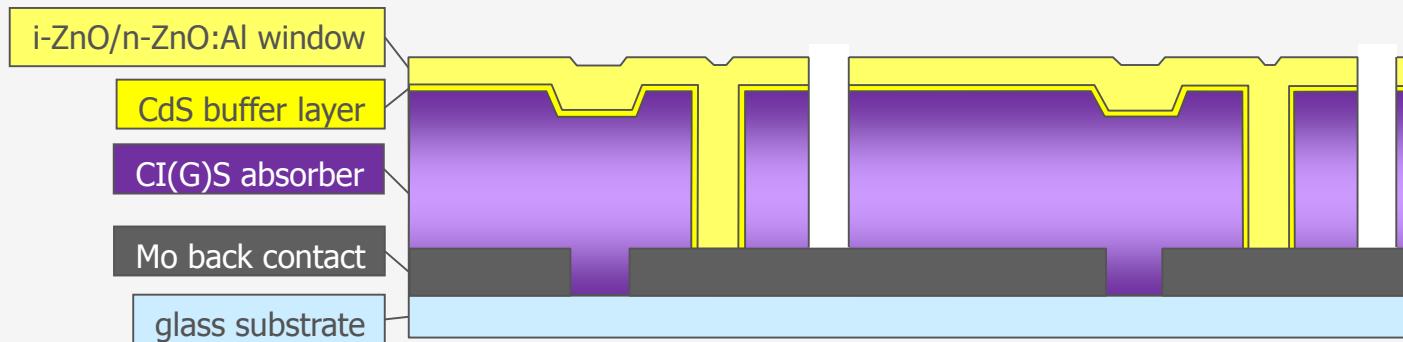
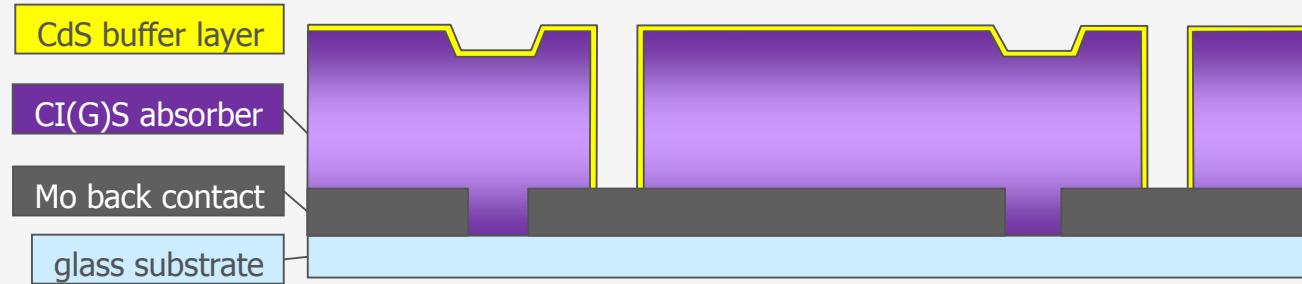
Flexible

SFL-MS:

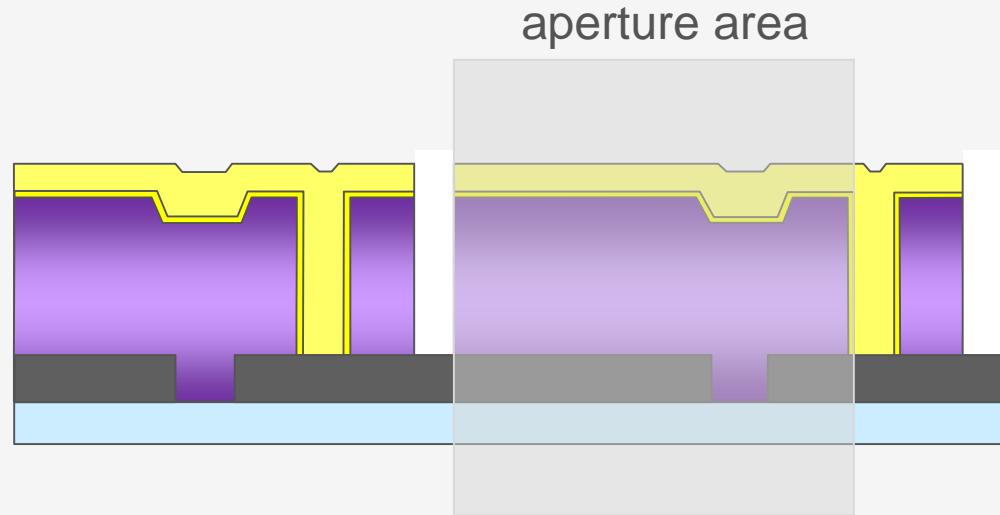
Eff: 20.4 %



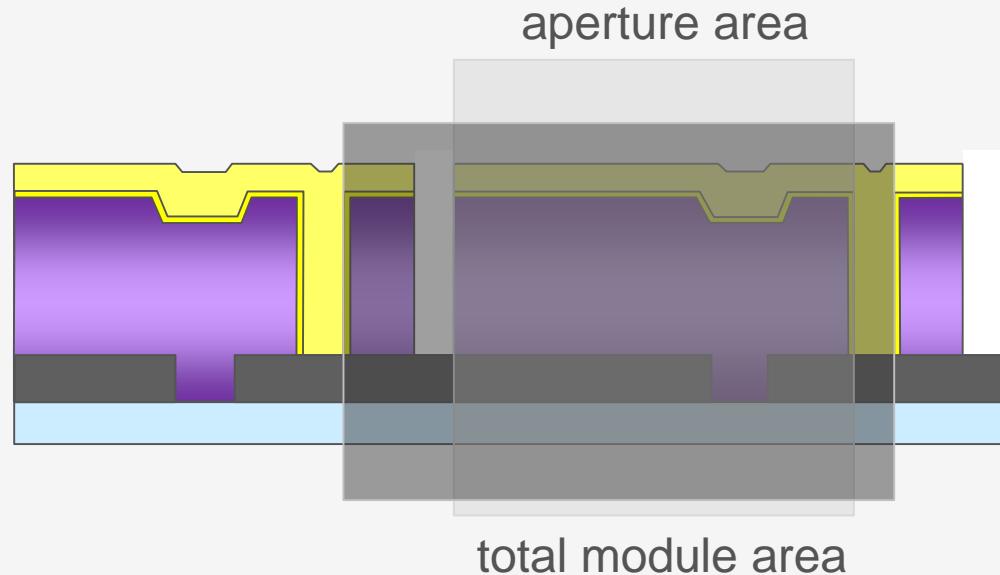


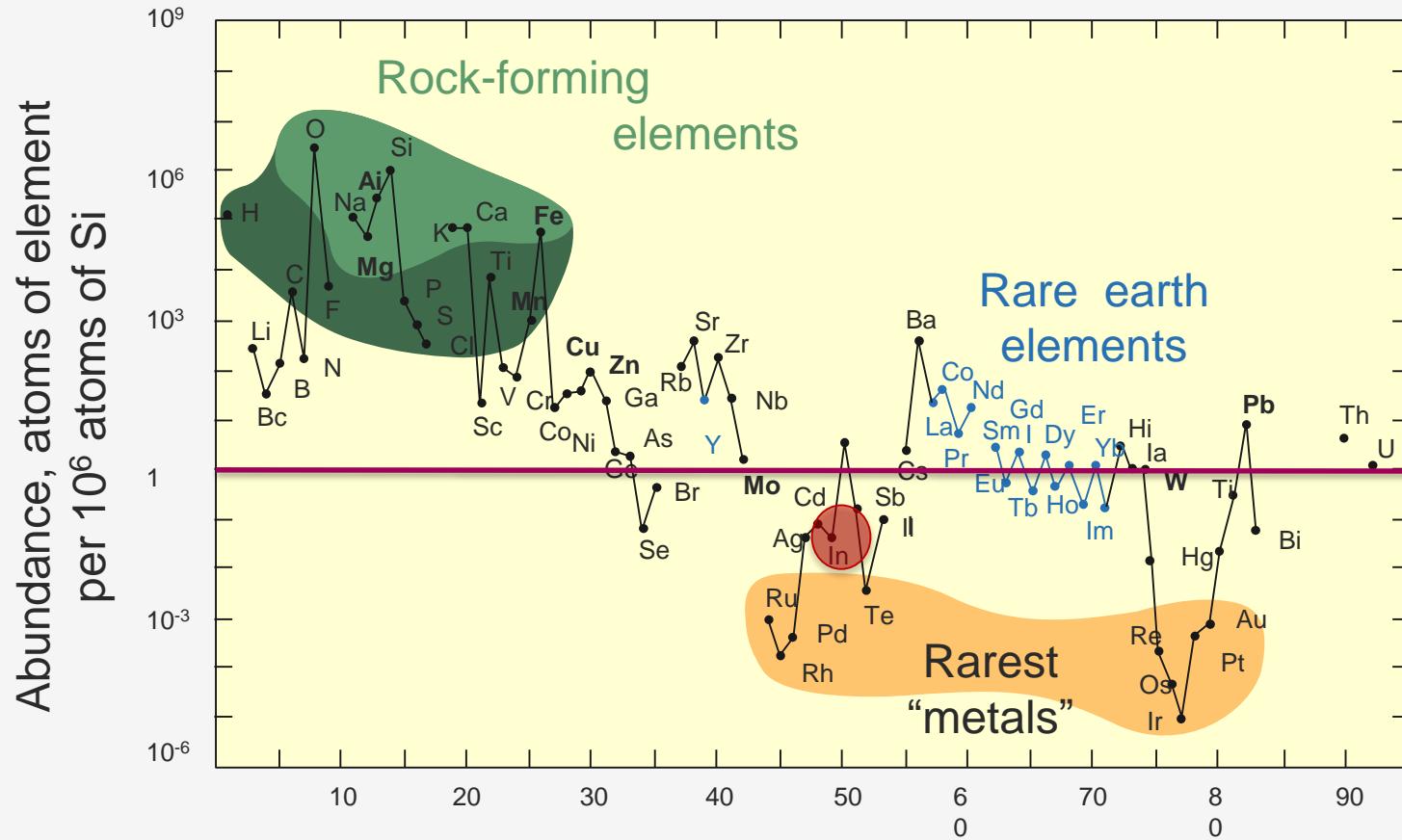


Module Efficiency



Module Efficiency





CZTS (CuZnSnS)

